(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
16 September 2010 (16.09.2010)

PCT

(10) International Publication Number
WO 2010/102686 A1

(51) International Patent Classification:
H01L 21/62 (2006.01)

(21) International Application Number:
PCT/EP2009/067919

(22) International Filing Date:
24 December 2009 (24.12.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0951452 9 March 2009 (09.03.2009) FR

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM,

[Continued on next page]

(54) Title: A METHOD OF PRODUCING A HETEROSTRUCTURE WITH LOCAL ADAPTATION OF THE THERMAL EXPANSION COEFFICIENT

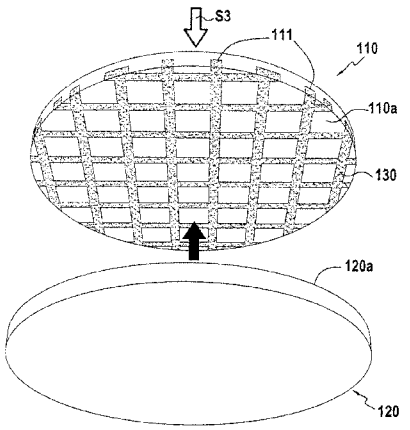


FIG.1C

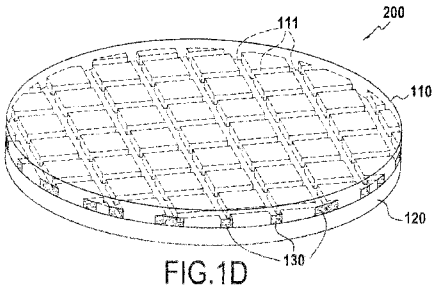


FIG.1D

(57) Abstract: A method of producing a heterostructure (200) comprising bonding at least one first substrate (110) having a first thermal expansion coefficient onto a second substrate (120) having a second thermal expansion coefficient, the first thermal expansion coefficient being different from the second thermal expansion coefficient. Prior to bonding, trenches (111) are formed in one of the two substrates from the bonding surface (110a) of the substrate (110). The trenches (111) are filled with a material (130) having a third thermal expansion coefficient lying between the first and second thermal expansion coefficients.

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TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*